

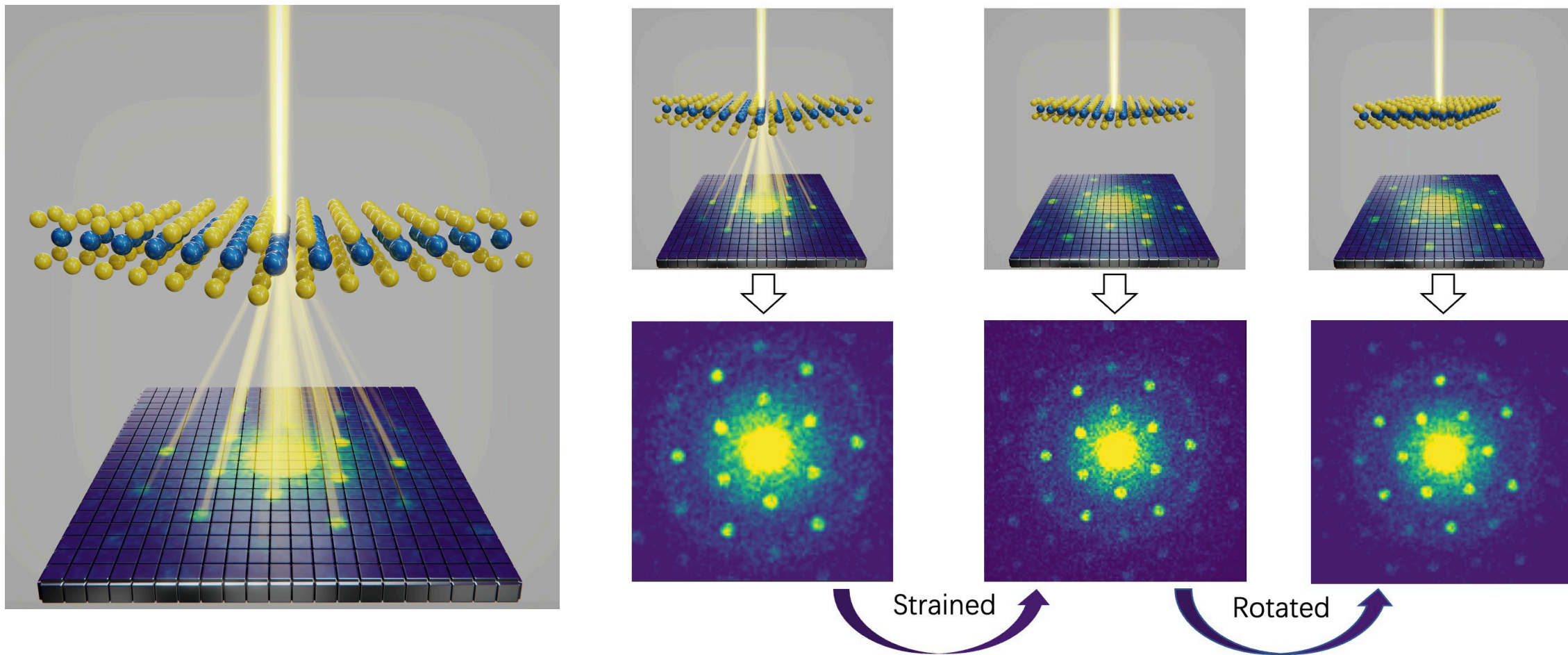
Cycle-Consistent Spatial Transforming Autoencoders

Joshua C. Agar
Drexel University

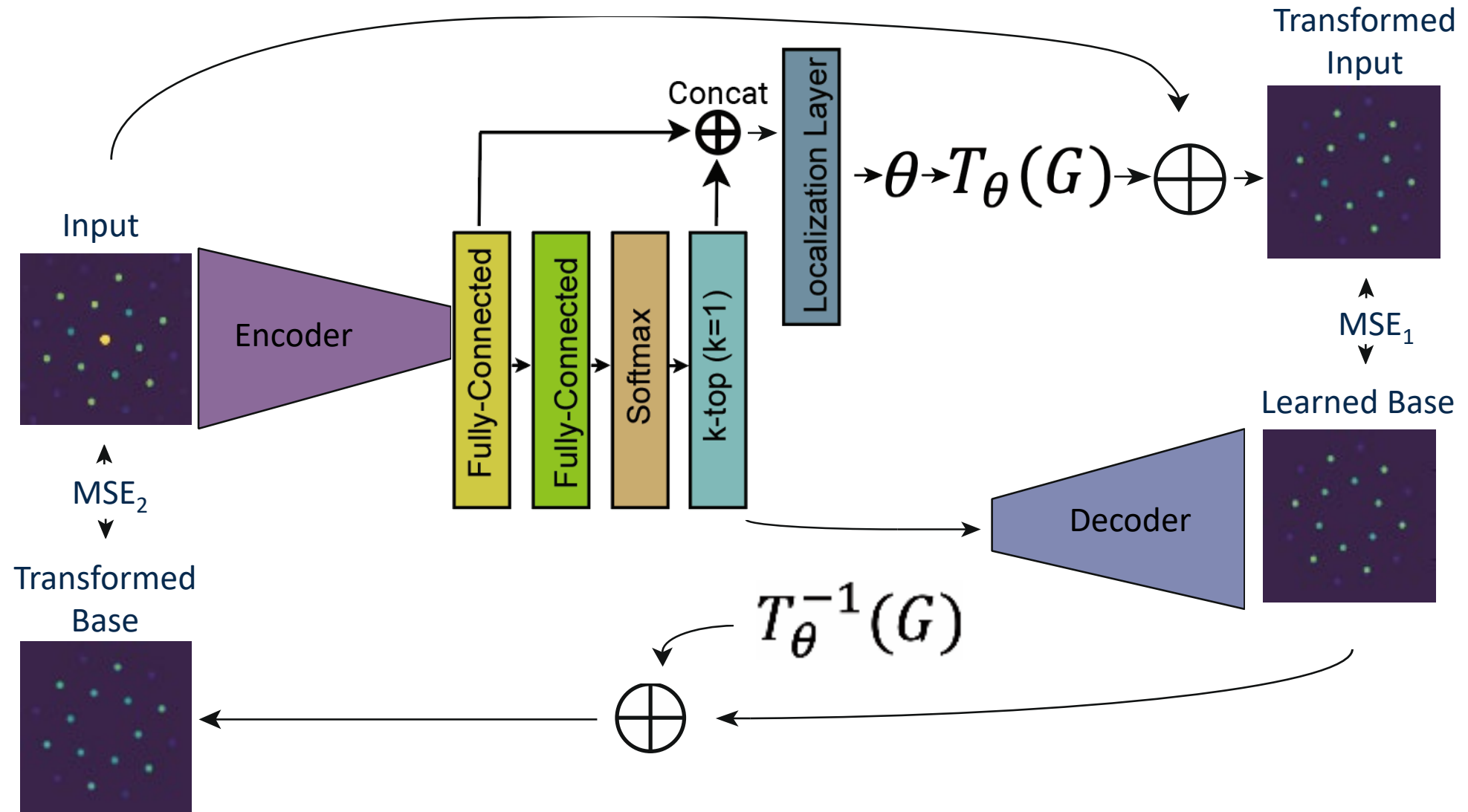
Department of Mechanical Engineering and Mechanics

Friday, September 8, 2023

Parsimonious Machine Learning

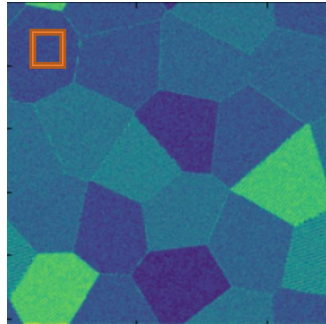


Cycle-Consistent Spatial Transforming Autoencoder



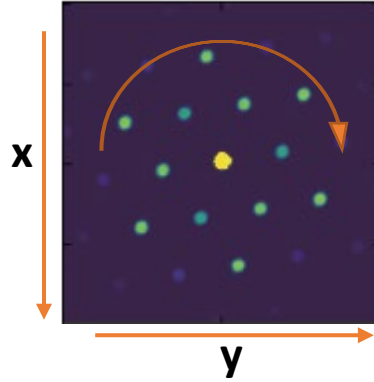
Simulated Noise-Free 4D-STEM

Sample domain
image



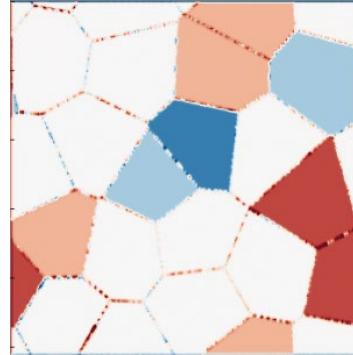
256 x 256

Random diffraction
image

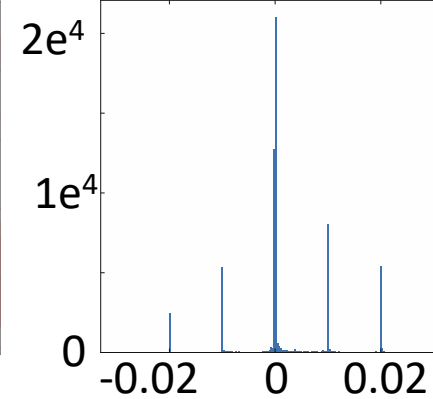


200 x 200

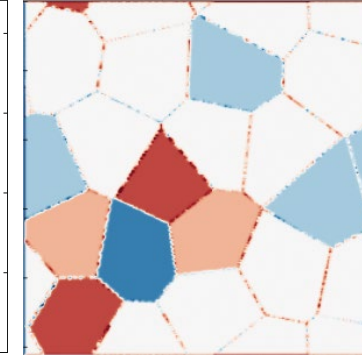
Strain x
mapping



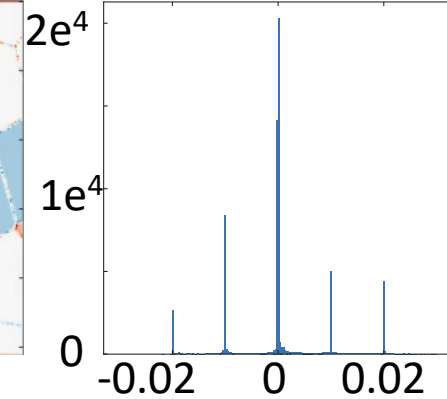
Strain x
histogram



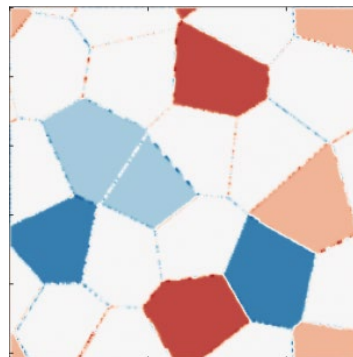
Strain y
mapping



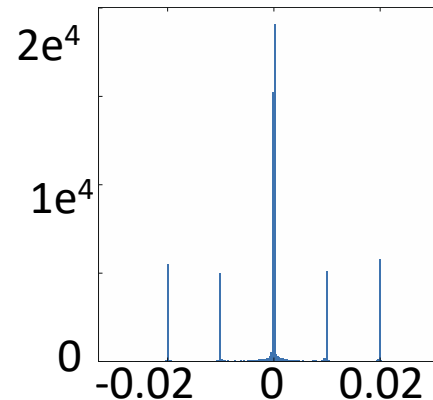
Strain y
histogram



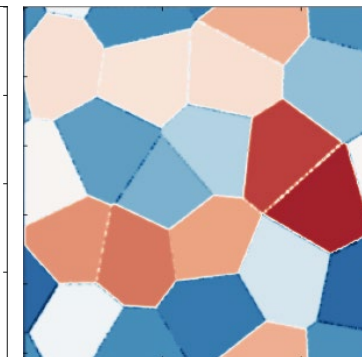
Strain xy
mapping



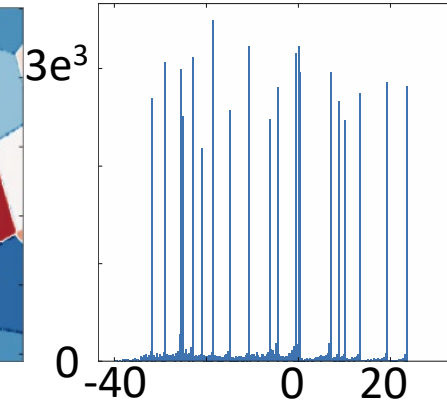
Strain xy
histogram



Rotation
mapping



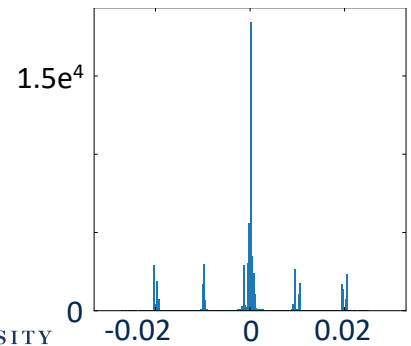
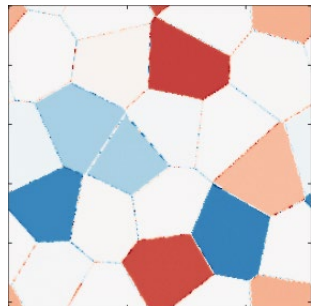
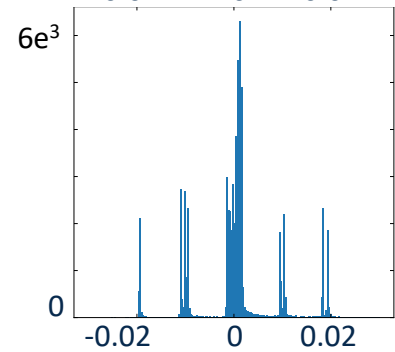
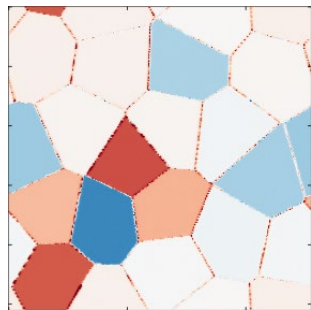
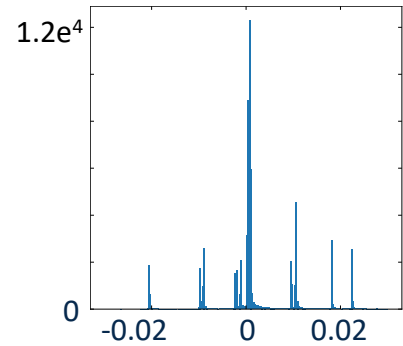
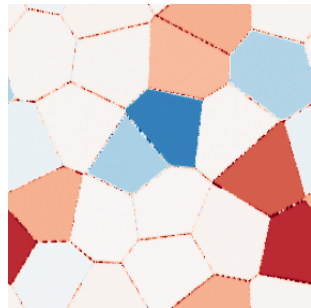
Rotation
histogram



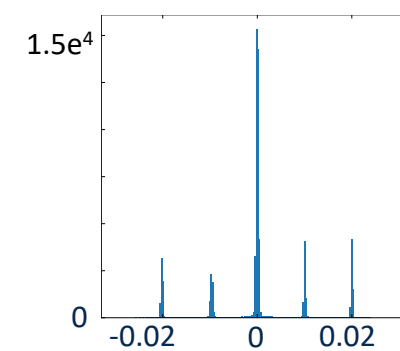
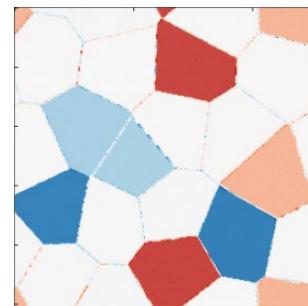
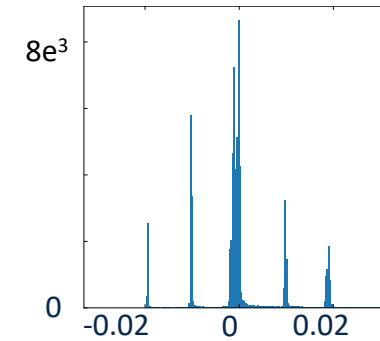
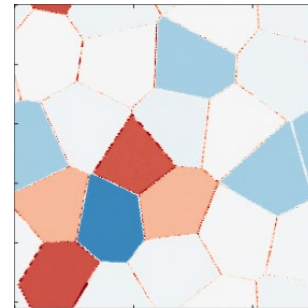
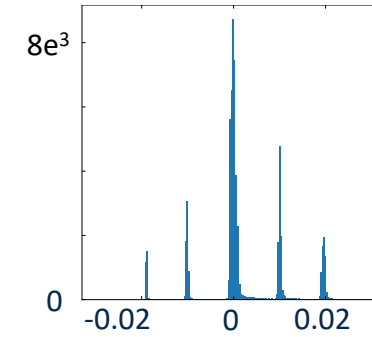
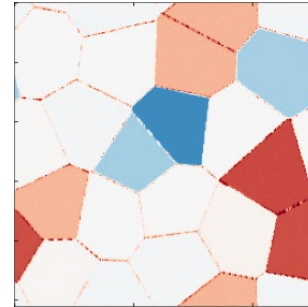
□ : Reference grain:
No rotation & strain

Comparison of py4DSTEM (Clean Data strain map)

py4DSTEM

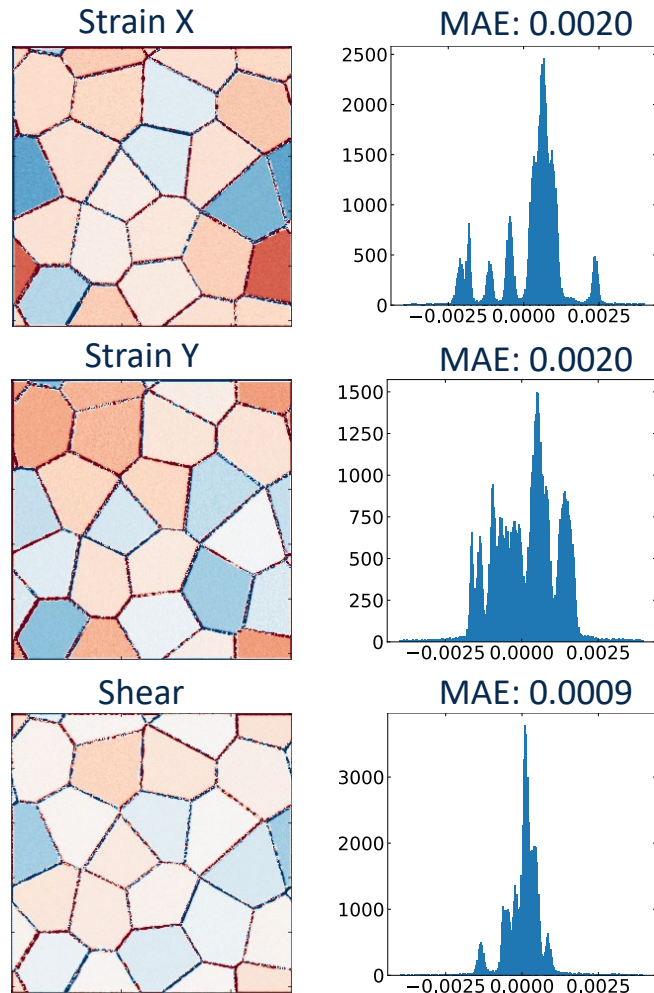


Neural Network

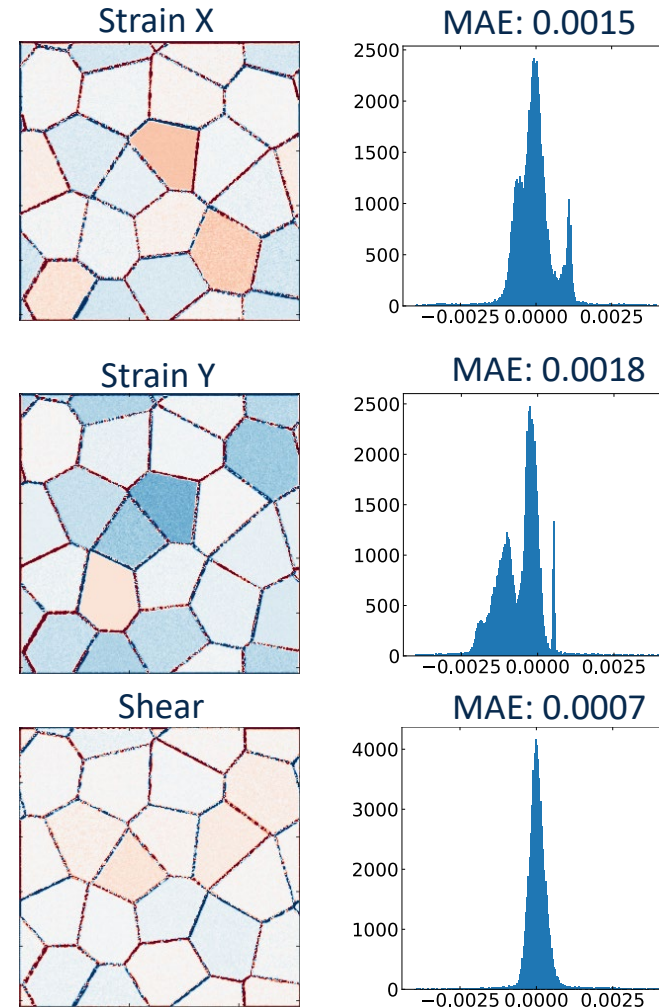


Visualize difference with Label (Map & Histogram)

py4DSTEM



Neural Network

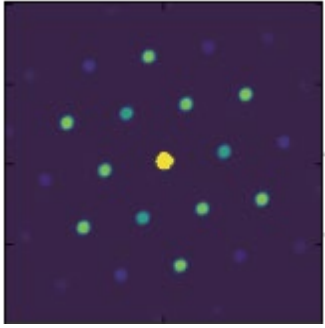


Comparison of py4DSTEM (Add 25% Background Noise)

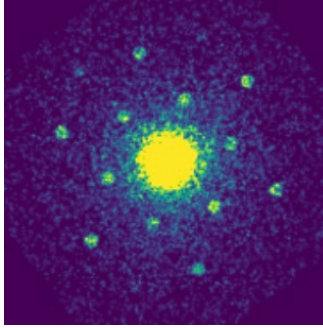
py4DSTEM

Neural Network

Noise-Free

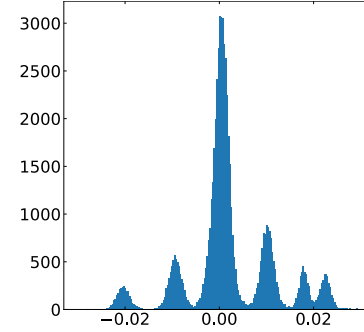
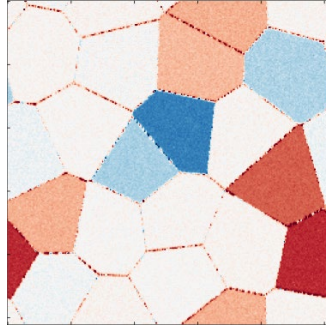


Add Noise

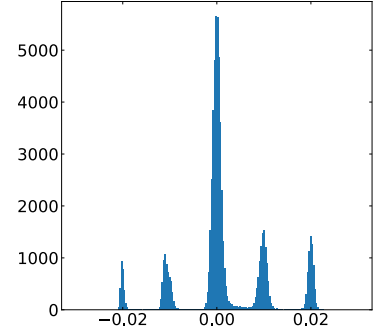
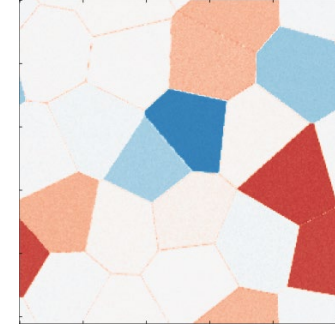


Add 25% Poisson Background Noise to each Diffraction Image

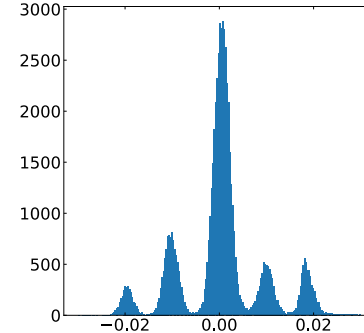
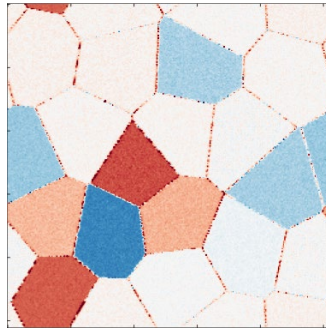
Strain X



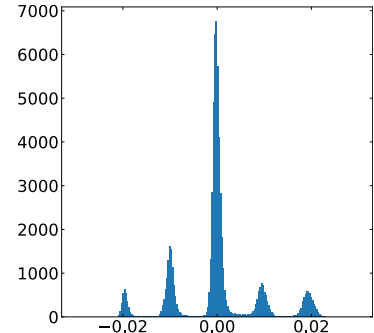
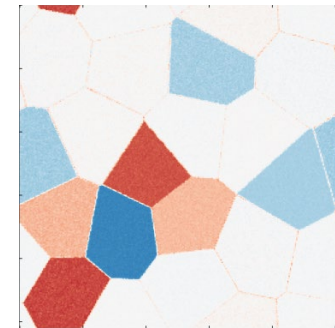
Strain X



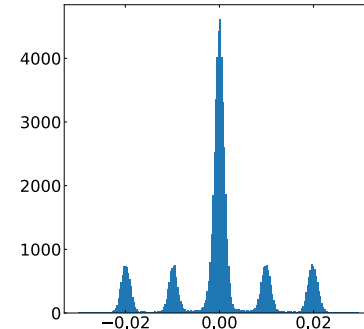
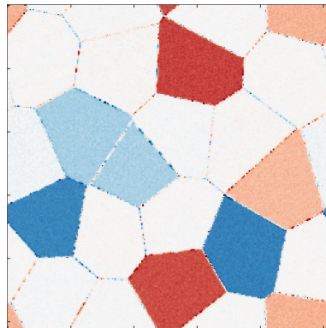
Strain Y



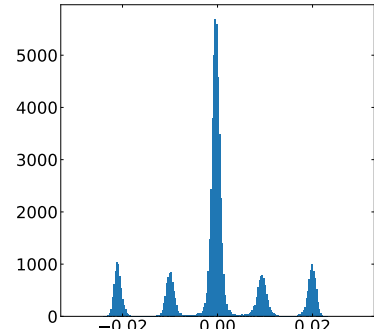
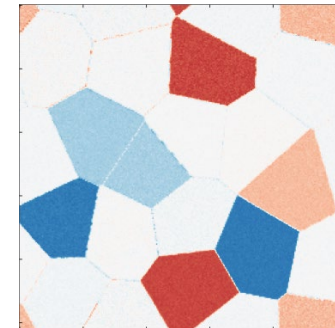
Strain Y



Shear

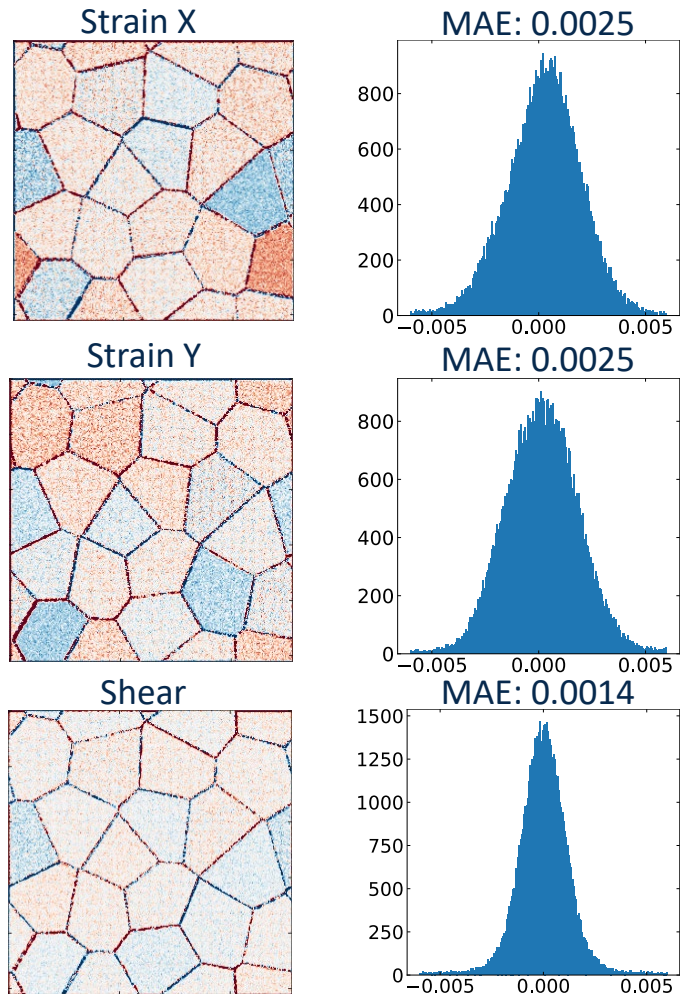


Shear

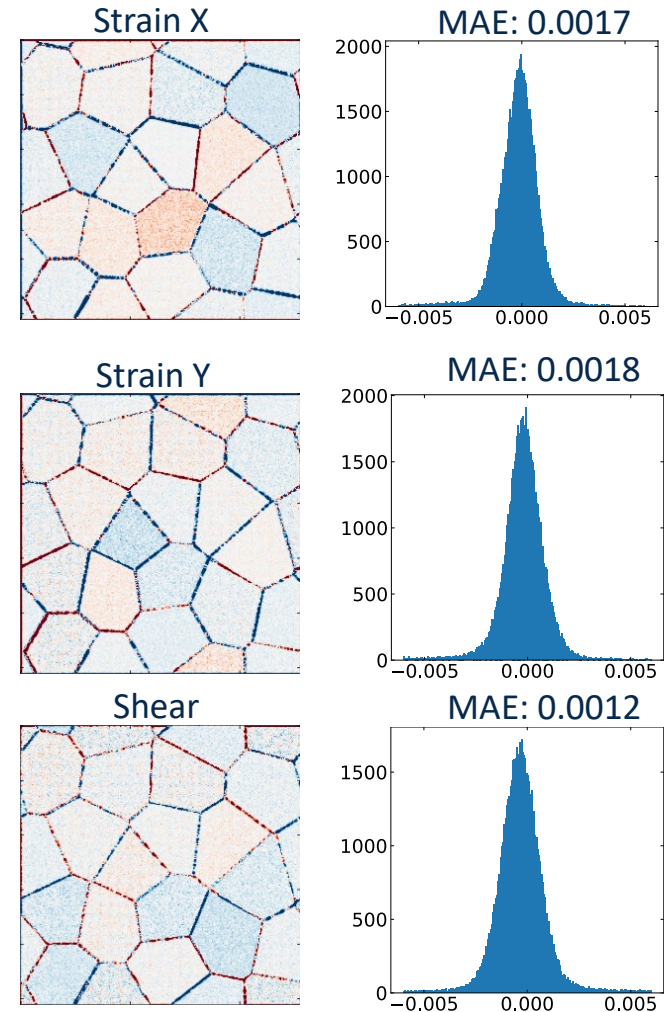


Visualize difference with Label (Map & Histogram)

py4DSTEM



Neural Network

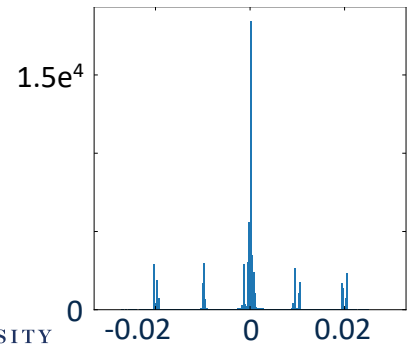
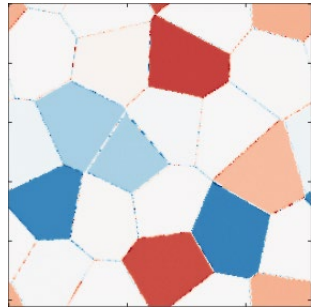
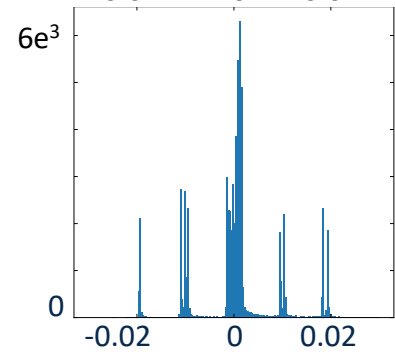
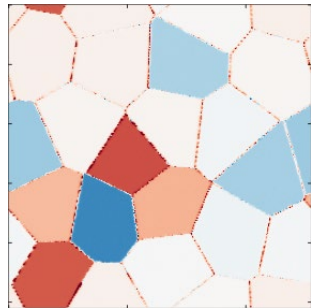
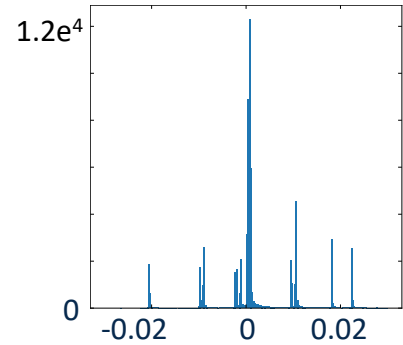
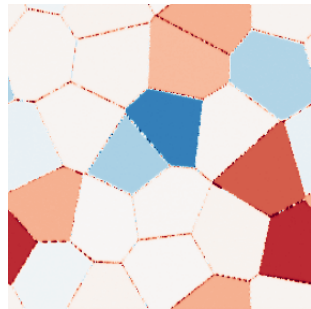


Noise Benchmark

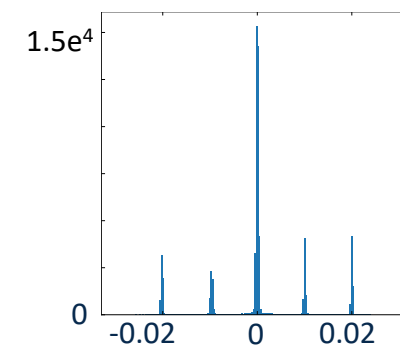
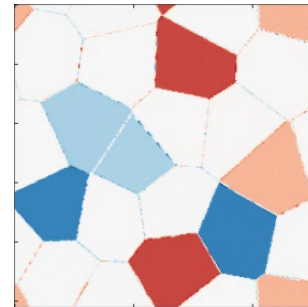
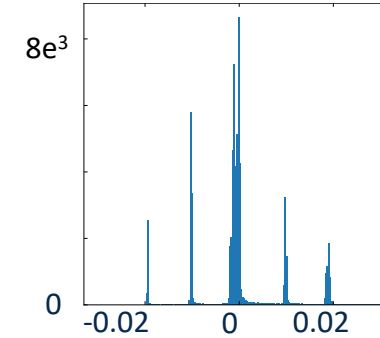
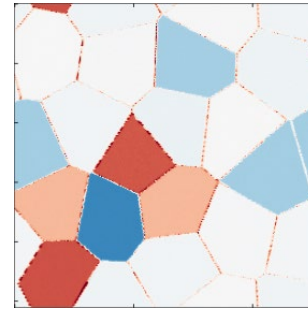
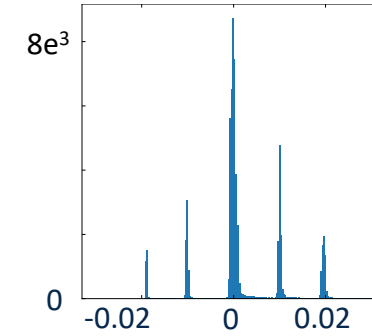
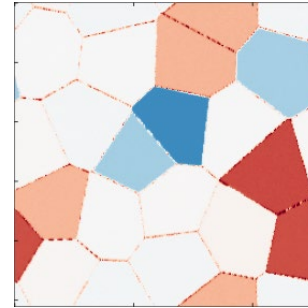
BKG noise intensity /Percentage	Strain X (MAE with Label) *1e-3		Strain Y (MAE with Label) *1e-3		Shear (MAE with Label) *1e-3	
	py4dstem	CC-ST-AE	py4dstem	CC-ST-AE	py4dstem	CC-ST-AE
0	2.0	1.5	2.0	1.8	0.9	0.7
5%	2.3	1.5	2.4	1.6	1.2	1.2
10%	2.3	1.5	2.4	1.6	1.3	1.0
15%	2.3	1.6	2.4	1.7	1.3	0.9
20%	2.4	1.7	2.5	1.7	1.4	1.0
25%	2.5	1.6	2.5	1.9	1.4	1.1
30%	2.5	1.6	2.6	1.7	1.4	1.2
35%	2.6	1.8	2.7	1.8	1.5	1.1
40%	2.7	1.7	2.7	1.8	1.6	1.3
45%	2.8	1.8	2.9	2.0	1.7	1.2

Comparison of py4DSTEM (Add 60% strain map)

py4DSTEM

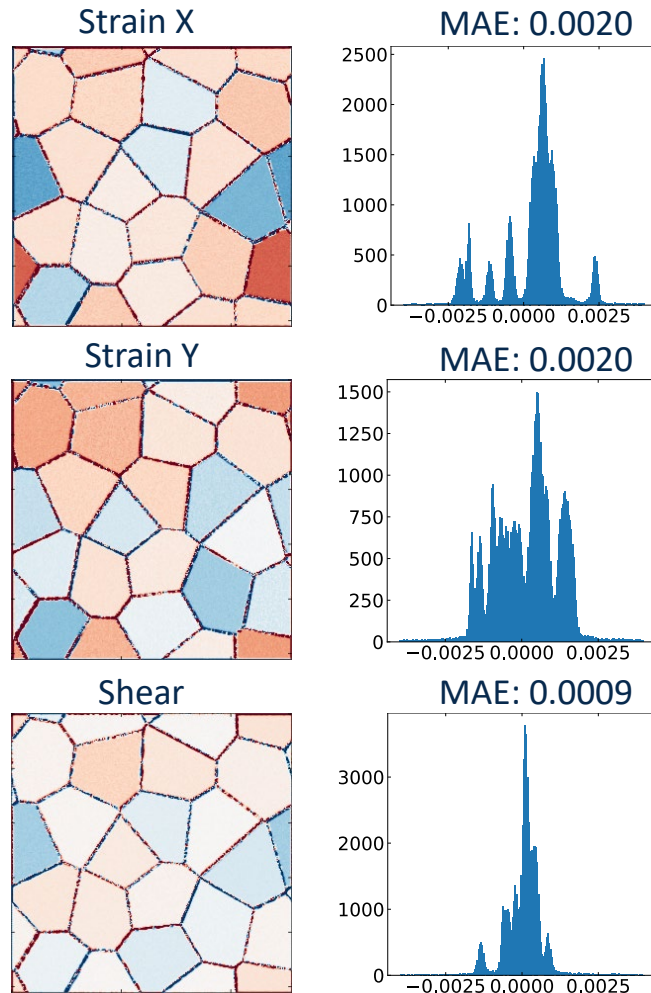


Neural Network

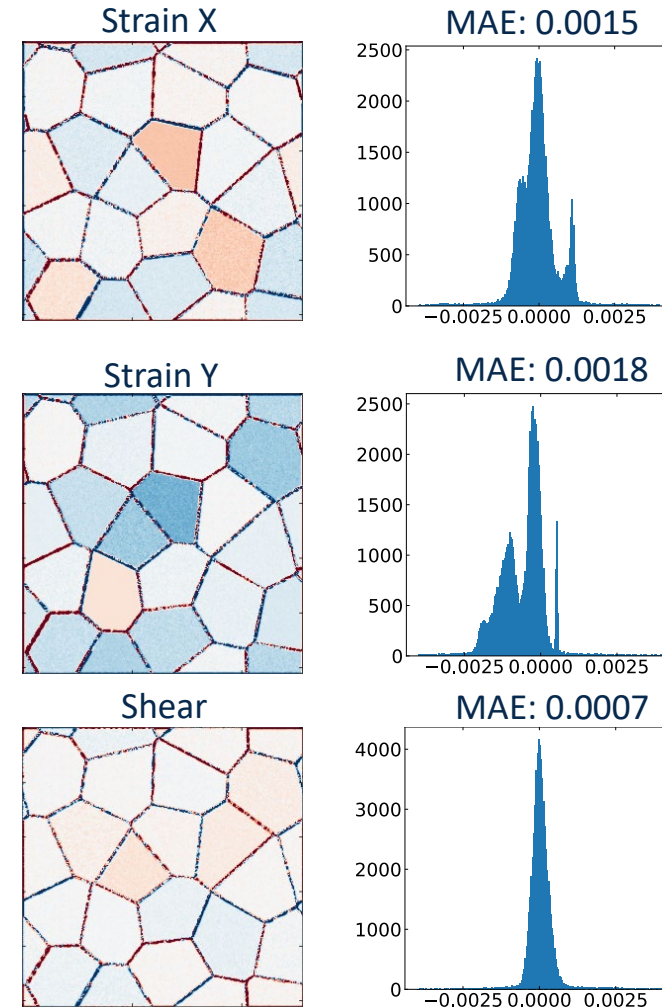


Visualize difference with Label (Map & Histogram)

py4DSTEM



Neural Network



Experimental Dataset: WSe₂WS₂ 4D-STEM

NANO LETTERS

Cite This: Nano Lett. 2018, 18, 3746–3751

pubs.acs.org/NanoLett

Letter

Strain Mapping of Two-Dimensional Heterostructures with Subpicometer Precision

Yimo Han,[†] Kayla Nguyen,^{†,§} Michael Cao,[†] Paul Cueva,[†] Saien Xie,^{†,‡} Mark W. Tate,^{||} Prafull Purohit,^{||} Sol M. Gruner,^{||,⊥,¶,∇} Jiwoong Park,[‡] and David A. Muller^{*,†,¶}

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^{||}Laboratory of Atomic and Solid State Physics, Cornell University, Ithaca, New York 14853, United States

[⊥]Physics Department, Cornell University, Ithaca, New York 14853, United States

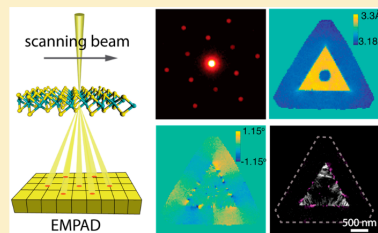
[¶]Kavli Institute at Cornell for Nanoscale Science, Ithaca, New York 14853, United States

[∇]Cornell High Energy Synchrotron Source, Cornell University, Ithaca, New York 14853, United States

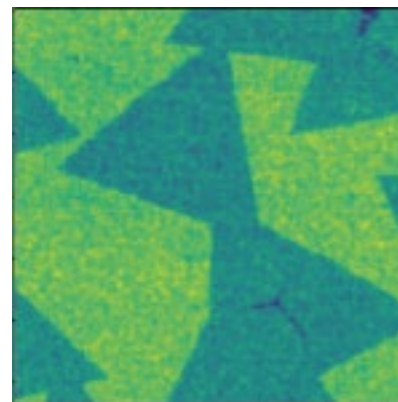
Supporting Information

ABSTRACT: Next-generation, atomically thin devices require in-plane, one-dimensional heterojunctions to electrically connect different two-dimensional (2D) materials. However, the lattice mismatch between most 2D materials leads to unavoidable strain, dislocations, or ripples, which can strongly affect their mechanical, optical, and electronic properties. We have developed an approach to map 2D heterojunction lattice and strain profiles with subpicometer precision and the ability to identify dislocations and out-of-plane ripples. We collected diffraction patterns from a focused electron beam for each real-space scan position with a high-speed, high dynamic range, momentum-resolved detector—the electron microscope pixel array detector (EMPAD). The resulting four-dimensional (4D) phase space data sets contain the full spatially resolved lattice information on the sample. By using this technique on tungsten disulfide (WS₂) and tungsten diselenide (WSe₂) lateral heterostructures, we have mapped lattice distortions with 0.3 pm precision across multimicron fields of view and simultaneously observed the dislocations and ripples responsible for strain relaxation in 2D laterally epitaxial structures.

KEYWORDS: EMPAD, STEM, 2D lateral heterostructure, strain, dislocation, ripple

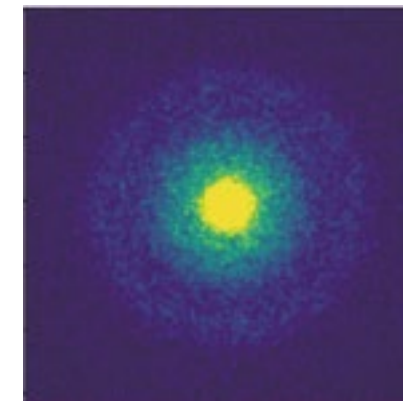


Sample Domain image

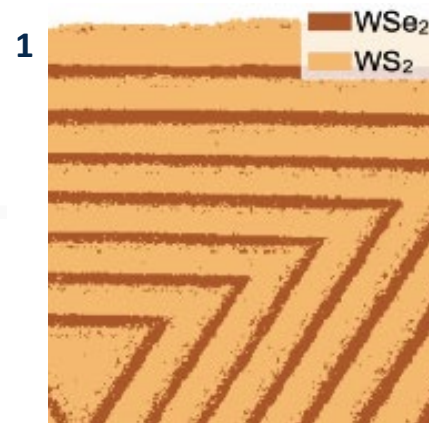


Random Diffraction image

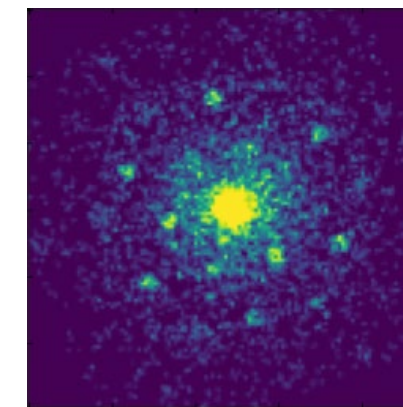
Background



theoretical Structure

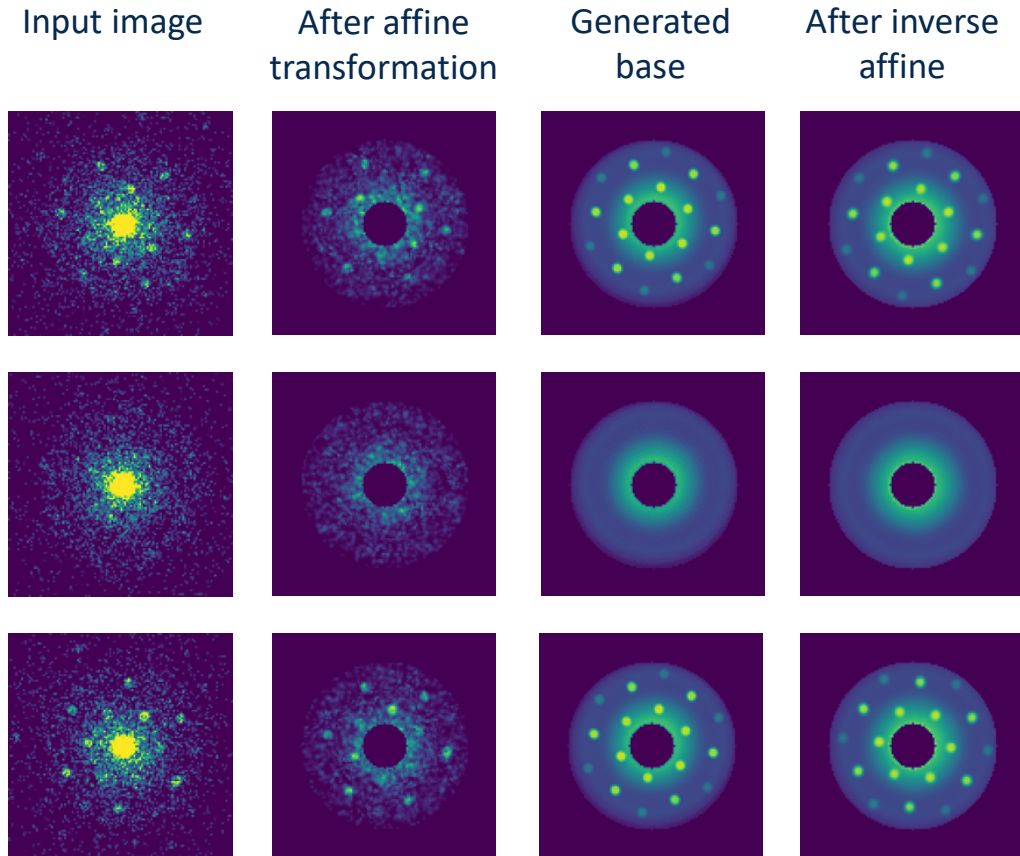


Sample



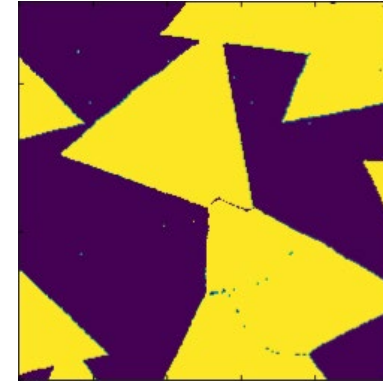
CC-ST-AE Training Results

Random Example

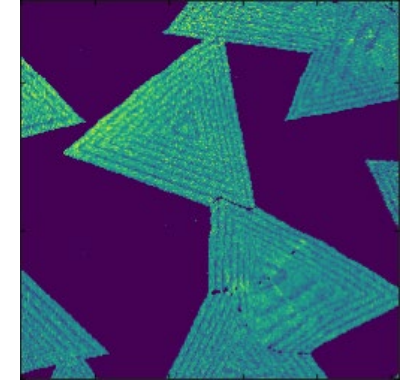


Classification & Strain map

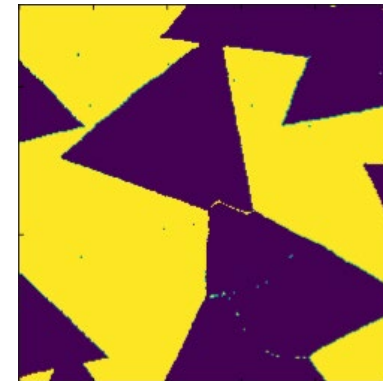
Sample region



Magnitude Map



Background



Histogram

